



MEMC 00-1400(2806.1)
PATENT

THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Robert J. Falster et al.
Serial No. 10/039,196
Filed January 2, 2002
Confirmation No. 7221

Art Unit 1765

For PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING
IMPROVED GATE OXIDE INTEGRITY

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April 8, 2002

TO THE COMMISSIONER OF PATENTS AND TRADEMARKS,

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INFORMATION DISCLOSURE STATEMENT

* In accordance with 37 C.F.R. 1.97 and 1.98 and MPEP 609, and in compliance with the duty of disclosure set forth in 37 C.F.R. 1.56, applicants submit copies of the references listed on the attached PTO/SB/08A for consideration by the Patent and Trademark Office in the above-entitled application and to be made of record therein.

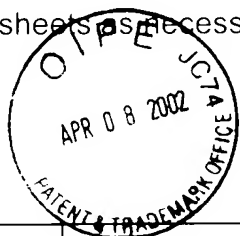
Respectfully submitted,

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PTO/SB/08A			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	10/039,196	
			Filing Date	January 2, 2002	
			Confirmation Number	7221	
			First Named Inventor	Robert J. Falster	
			Group Art Unit	1765	
			Examiner Name		
Sheet	1	of	2	Attorney Docket No.	MEMC 00-1400 (2806.1)



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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
	1	5,919,302		Falster et al.	07-06-1999
	2	5,994,761		Falster et al.	11-30-1999
	3	6,180,220		Falster et al.	01-30-2001
	4	6,191,010		Falster	02-20-2001
	5	6,254,672		Falster et al.	07-03-2001
	6	6,287,380		Falster et al.	09-11-2001
	7	6,336,968		Falster	01-08-2002
OTHER ART - NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ³
	8	R. FALSTER "The Phenomenology of Dielectric Breakdown in Thin Silicon Dioxide Films: Al Cathodes and p-type Si Anodes" J. Appl. Phys., Vol. 66, No. 7 (1989) pp. 3355-3370.			
	9	R. FALSTER et al. "On the Properties of the Intrinsic Point Defects in Silicon: A Perspective from Crystal Growth and Wafer Processing" Phys. Stat. Sol. (b), Vol. 222, No. 1 (2000) pp. 219-244.			

Examiner Signature	Date Considered
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*EXAMINER Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (W, PC Standard ST, J³). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST-16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached.

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Sheet 2 of 2	Attorney Docket No.	MEMC 00-1400 (2806.1)	



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OTHER ART - NON PATENT LITERATURE DOCUMENTS

10	T. SINNO et al. "Point Defect Dynamics and the Oxidation-Induced Stacking-Fault Ring in Czochralski-Grown Silicon Crystals" J. Electrochem. Soc., Vol. 145, No. 1 (1998) pp. 302-318.	
11	A. VIRZI "Computer Modelling of Heat Transfer in Czochralski Silicon Crystal Growth" J. of Crystal Growth, Vol. 112, No. 4 (1991) pp. 699-722.	
12	V. VORONKOV et al. "Grown-in Microdefects, Residual Vacancies and Oxygen Precipitation Bands in Czochralski Silicon" J. of Crystal Growth, Vol. 204 (1999) pp. 462-474.	
13	V. VORONKOV et al. "Vacancy and Self-interstitial Concentration Incorporated into Growing Silicon Crystals" J. of Applied Physics, Vol. 86, No. 11 (1999) pp. 2975-2982.	
14	V. VORONKOV et al. "Vacancy-type Microdefect Formation in Czochralski Silicon" J. of Crystal Growth, Vol. 194 (1998) pp. 76-88.	

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